IN THE CLAIMS

Please amend the claims as follows:

- 1. (Original): A heat-conducting multilayer substrate comprising: at least a Cu circuitry layer of at least 99.999% purity and a ceramic layer.
- 2. (Original): A heat-conducting multilayer substrate comprising: a ceramic layer, a Cu circuitry layer having at least 99.999% purity provided on one side of said ceramic layer, and a high-purity metal layer provided on the other side of the ceramic layer.
- 3. (Original): A heat-conducting multilayer substrate according to claim 2, wherein the high-purity metal layer is a Cu metal layer of at least 99.999% purity.
- 4. (Original): A power module substrate comprising: an insulating substrate, a circuitry layer laminated on one side of said insulating substrate, a metal layer laminated on the other side of said insulating substrate, a semiconductor chip loaded onto the circuitry layer by means of solder, and a radiator joined to the metal layer; wherein, the circuitry layer and the metal layer are composed of copper of at least 99.999% purity.
- 5. (Original): A power module substrate according to claim 4, wherein the radiator is joined to the metal layer by solder, brazing or a diffused bonding.
- 6. (Original): A power module substrate according to claim 4, wherein the insulating substrate is composed of AlN, Al₂O₃, Si₃N₄ or SiC.

- 7. (Original): A power module substrate according to claim 5, wherein the insulating substrate is composed of AlN, Al₂O₃, Si₃N₄ or SiC.
- 8. (Original): A power module substrate according to claim 4, wherein the circuitry layer and the metal layer release stress within 24 hours at 100°C.
- 9. (Original): A power module substrate according to claim 5, wherein the circuitry layer and the metal layer release stress within 24 hours at 100°C.
- 10. (Original): A power module substrate according to claim 6, wherein the circuitry layer and the metal layer release stress within 24 hours at 100°C.
- 11. (Original): A power module substrate according to claim 4, wherein elongation during rupture of the circuitry layer and the metal layer is from 20% to 30% within the range of -40°C to 150°C.
- 12. (Original): A power module substrate according to claim 5, wherein elongation during rupture of the circuitry layer and the metal layer is from 20% to 30% within the range of -40°C to 150°C.
- 13. (Original): A power module substrate according to claim 6, wherein elongation during rupture of the circuitry layer and the metal layer is from 20% to 30% within the range of -40°C to 150°C.

- 14. (Original): A power module substrate according to claim 4, wherein the thickness of the circuitry layer and the metal layer is from 0.04 mm to 1.0 mm.
- 15. (Original): A power module substrate according to claim 5, wherein the thickness of the circuitry layer and the metal layer is from 0.04 mm to 1.0 mm.
- 16. (Original): A power module substrate according to claim 6, wherein the thickness of the circuitry layer and the metal layer is from 0.04 mm to 1.0 mm.
- 17. (Currently Amended): A power module substrate according to claim 4, wherein the conductivity of the circuitry layer and the metal layer is at least 99% IACS under the International Annealed Copper Standard (IACS).
- 18. (Original): A power module substrate according to claim 5, wherein the conductivity of the circuitry layer and the metal layer is at least 99% IACS.
- 19. (Original): A power module substrate according to claim 6, wherein the conductivity of the circuitry layer and the metal layer is at least 99% IACS.
- 20. (Original): A power module substrate according to claim 4, wherein the average particle diameter of crystalline particles of the circuitry layer and the metal layer is from 1.0 mm to 30 mm.

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- 21. (Original): A power module substrate according to claim 5, wherein the average particle diameter of crystalline particles of the circuitry layer and the metal layer is from 1.0 mm to 30 mm.
- 22. (Original): A power module substrate according to claim 6, wherein the average particle diameter of crystalline particles of the circuitry layer and the metal layer is from 1.0 mm to 30 mm.